AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

- 1. (original) A semiconductor device comprising:
- a first conducting film formed on a semiconductor substrate;
- a dielectric deposited on said first conducting film;
- a second conducting film formed on said dielectric,
 wherein said dielectric comprises a polycrystalline
 oxide having a plurality of crystal grains and an amorphous
 oxide present at the boundaries formed between said crystal
 grains.
- (original) A semiconductor device comprising:
- a first conducting film formed on a semiconductor substrate;
 - a dielectric deposited on said first conducting film;
 - a second conducting film formed on said dielectric,

wherein said dielectric comprises a polycrystalline oxide with a first crystallization temperature, having a

plurality of crystal grains, and an amorphous oxide with a crystallization temperature higher than the first crystallization temperature present at boundaries formed between said crystal grains.

- 3. (original) A semiconductor device comprising:
- a first conducting film formed on a semiconductor substrate;
- a dielectric deposited on said first conducting film; and
- a second conducting film formed on said dielectric,
 wherein said dielectric comprises a polycrystalline
 oxide with a first dielectric constant and first
 crystallization temperature, having a plurality of crystal
 grains, and an amorphous oxide, having a lower dielectric
 constant than said first dielectric constant and a higher
 crystallization temperature than said first
 crystallization temperature, present at boundaries formed
 between said crystal grains.
- 4. (original) A semiconductor device having a capacitor comprising:

- a first electrode of said capacitor comprising a first conducting film formed on a semiconductor substrate;
 - a dielectric deposited on said first electrode; and
- a second electrode of said capacitor comprising a second conducting film formed on said dielectric,

wherein the dielectric comprises a polycrystalline oxide having a plurality of crystal grains and an amorphous oxide present at boundaries formed between said crystal grains.

- 5. (original) A semiconductor device according to claim 1, wherein said polycrystalline oxide comprises niobium pentoxide.
- 6. (original) A semiconductor device according to claim 1, wherein said polycrystalline oxide comprises niobium pentoxide, and the amorphous oxide comprises tantalum pentoxide.
- 7. (original) A semiconductor device according to claim 1, wherein the content of the amorphous oxide in said dielectric is from 5% to 50%.

- 8. (original) A semiconductor device according to claim 1, wherein the amorphous oxide comprises at least one oxide selected from among tantalum, silicon, titanium, and tungsten.
- 9. (original) A semiconductor device according to claim 1, wherein the film thickness of said dielectric is from 5 nm to 20 nm.
- 10. (original) A semiconductor device according to claim
 4, wherein said first electrode comprises a material
 selected from ruthenium, platinum, copper, titanium
 nitride, tantalum nitride and tungsten nitride.
- 11. (original) A semiconductor device according to claim
 4, wherein said first electrode comprises polycrystalline
 silicon and a silicon oxide film exists between said first
 electrode and said dielectric.

Claims 12-19 (cancelled)

- 20. (original) A semiconductor device according to claim 2, wherein said polycrystalline oxide comprises niobium pentoxide.
- 21. (original) A semiconductor device according to claim
 2, wherein said polycrystalline oxide comprises niobium
 pentoxide, and the amorphous oxide comprises tantalum
 pentoxide.
- 22. (original) A semiconductor device according to claim 2, wherein the proportion of the amorphous oxide in said dielectric is from 5% to 50%.
- 23. (original) A semiconductor device according to claim
 2, wherein the amorphous oxide comprises at least one oxide
 selected from among tantalum, silicon, titanium, and
 tungsten.
- 24. (original) A semiconductor device according to claim
 2, wherein the film thickness of said dielectric is from 5
 nm to 20 nm.

- 25. (original) A semiconductor device according to claim 3, wherein said polycrystalline oxide comprises niobium pentoxide.
- 26. (original) A semiconductor device according to claim

 3, wherein said polycrystalline oxide comprises niobium

 pentoxide, and the amorphous oxide comprises tantalum

 pentoxide.
- 27. (original) A semiconductor device according to claim 3, wherein the proportion of the amorphous oxide in said dielectric is from 5% to 50%.
- 28. (original) A semiconductor device according to claim

 3, wherein the amorphous oxide comprises at least one
 oxide selected from among tantalum, silicon, titanium, and
 tungsten.
- 29. (original) A semiconductor device according to claim
 3, wherein the film thickness of said dielectric is from 5
 nm to 20 nm.

- 30. (original) A semiconductor device according to claim 4, wherein said polycrystalline oxide comprises niobium pentoxide.
- 31. (original) A semiconductor device according to claim
 4, wherein said polycrystalline oxide comprises niobium
 pentoxide, and the amorphous oxide comprises tantalum
 pentoxide.
- 32. (original) A semiconductor device according to claim 4, wherein the proportion of the amorphous oxide in said dielectric is from 5% to 50%.
- 33. (original) A semiconductor device according to claim
 4, wherein the amorphous oxide comprises at least one oxide
 selected from among tantalum, silicon, titanium, and
 tungsten.
- 34. (original) A semiconductor device according to claim
 4, wherein the film thickness of said dielectric is from 5
 nm to 20 nm.

Claims 35-39 (cancelled)